

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A light-emitting apparatus, comprising:
 - a primary light source comprising a GaN semiconductor light-emitting device that emits a first light of a wavelength of 380 nm to 500 nm, said GaN semiconductor light-emitting device comprising:
 - a single reflective layer; and
 - a transparent electrode disposed above said single reflective layer; and
 - a leadframe comprising a cup portion including a bottom surface on which said GaN semiconductor light-emitting device is mounted;
 - a secondary light source comprising a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; and Y₂O₂S:Ce, and a fluorescent material resin, said fluorescent material being dispersed within said fluorescent material resin, and said fluorescent material resin being contained in said cup portion; and
 - a sealing member that focuses light emitted from said light-emitting apparatus, said sealing member being disposed above said secondary light source,wherein said fluorescent material absorbs said first light of a first wavelength and emits a second light of a second wavelength, which is greater than said first wavelength.
2. (Previously Presented) A light-emitting apparatus according to claim 1, wherein
 - said secondary light source is disposed above said primary light source,
 - a part of said first light emitted by said primary light source is transmitted through said fluorescent material resin, and
 - another part of said first light emitted by said primary light source is absorbed by said fluorescent material, said fluorescent material then emits said second light, and said second light emitted by said fluorescent material and said first light emitted by said primary light source are mixed, to thereby generate a mixed light, emitted from said light-emitting apparatus, that is different in luminescent color from said first light emitted by said primary light source.

3. (Previously Presented) A light-emitting apparatus according to claim 2, wherein said fluorescent material resin comprises at least one of epoxy resin, silicone resin, urea resin, and glass.
4. (Canceled)
5. (Canceled)
6. (Previously Presented) A light-emitting apparatus according to claim 1, wherein said sealing member comprises at least one of epoxy resin, silicone resin, urea resin, and glass.
7. (Previously Presented) A light-emitting apparatus according to claim 1, wherein said sealing member is shaped like a bullet.
8. (Previously Presented) A light-emitting apparatus according to claim 2, wherein a concentration of said fluorescent material changes within said fluorescent material resin, as a function of distance to said GaN semiconductor light-emitting device.
9. (Previously Presented) A light-emitting apparatus according to claim 1, wherein said fluorescent material resin and said sealing member comprise one material.
10. (Previously Presented) A light-emitting apparatus according to claim 2, wherein said GaN semiconductor light-emitting device comprises a chip.
11. (Previously Presented) A light-emitting apparatus, comprising:
 - a primary light source comprising a GaN semiconductor light-emitting device that emits a first light of a wavelength of 380 nm to 500 nm, said GaN semiconductor light-emitting device, comprising:
 - a single reflective layer; and
 - a transparent electrode disposed above said single reflective layer; and

a leadframe comprising a cup portion including a bottom surface on which said GaN semiconductor light-emitting device is mounted;

a secondary light source comprising a fluorescent material that comprises at least one of ZnS:Eu and Y₂O₂S:Ce, and a fluorescent material resin, said fluorescent material being dispersed within said fluorescent material resin, and said fluorescent material resin being contained in said cup portion; and

a sealing member that focuses light emitted from said light-emitting apparatus, said sealing member being disposed above said secondary light source,

wherein said fluorescent material absorbs said first light of a first wavelength and emits said second light of a second wavelength, which is greater than said first wavelength.

12. (Previously Presented) A light-emitting apparatus according to claim 11, wherein said secondary light source is disposed above said primary light source,

a part of said first light emitted by said primary light source is transmitted through said fluorescent material resin, and

another part of said first light emitted by said primary light source is absorbed by said fluorescent material, said fluorescent material then emits said second light, and said second light emitted by said fluorescent material and said first light emitted by said primary light source are mixed, to thereby generate a mixed light, emitted from said light-emitting apparatus, that is different in luminescent color from said first light emitted by said primary light source.

13. (Previously Presented) A light-emitting apparatus according to claim 12, wherein said fluorescent material resin comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

14. (Canceled)

15. (Canceled)

16. (Previously Presented) A light-emitting apparatus according to claim 11, wherein said sealing member comprises at least one of epoxy resin, silicone resin, urea resin, and glass.

17. (Previously Presented) A light-emitting apparatus according to claim 11, wherein said sealing member is shaped like a bullet.

18. (Previously Presented) A light-emitting apparatus according to claim 12, wherein a concentration of said fluorescent material changes within said fluorescent material resin, as a function of distance to said GaN semiconductor light-emitting device.

19. (Previously Presented) A light-emitting apparatus according to claim 11, wherein said fluorescent material resin and said sealing member comprise one material.

20. (Previously Presented) A light-emitting apparatus according to claim 12, wherein said GaN semiconductor light-emitting device comprises a chip.

21. (Previously Presented) A light-emitting apparatus, comprising:
a first light source comprising a GaN semiconductor light-emitting device that emits a blue light, said GaN semiconductor light-emitting device, comprising:
a single reflective layer; and
a transparent electrode disposed above said single reflective layer; and
a leadframe comprising a cup portion including a bottom surface on which said GaN semiconductor light-emitting device is mounted;
a second light source including a first fluorescent material that absorbs said blue light emitted by said first light source and emits a green light and a fluorescent material resin, said first fluorescent material being dispersed within said fluorescent material resin, and said fluorescent material resin being contained in said cup portion;
a sealing member that focuses light emitted from said light-emitting apparatus, said sealing member being disposed above said secondary light source; and
a third light source that emits a red light,

wherein said blue light emitted by said first light source, said green light emitted by said second light source, and said red light emitted by said third light source are mixed to thereby generate white light.

22. (Previously Presented) A light-emitting apparatus according to claim 21, wherein said first fluorescent material comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; ZnS:Eu; and $Y_2O_3S:Ce$.

23. (Canceled)

24. (Canceled)

25. (Original) A light-emitting apparatus according to claim 21, wherein said third light source includes a semiconductor light-emitting device for emitting red light.

26. (Previously Presented) A light-emitting apparatus according to claim 41, wherein said first fluorescent material and said second fluorescent material are dispersed in said fluorescent material resin, which is disposed above said GaN semiconductor light-emitting device,

a part of said blue light emitted by said first light source is transmitted through said fluorescent material resin, and

another part of said blue light emitted by said first light source is absorbed by said first fluorescent material, which emits said green light, and said second fluorescent material, which emits said red light, and said blue light emitted by said first light source, said green light emitted by said first fluorescent material, and said red light emitted by said second fluorescent material are mixed, to thereby generate a mixed light, emitted from said light-emitting apparatus, different in luminescent color from the said blue light emitted from said first light source.

27. (Previously Presented) A light-emitting apparatus according to claim 26, wherein said fluorescent material resin comprises at least one of epoxy resin, silicone resin, urea resin, and glass.
28. (Previously Presented) A light-emitting apparatus according to claim 26, wherein said fluorescent material resin is disposed above said GaN semiconductor light-emitting device.
29. (Canceled)
30. (Previously Presented) A light-emitting apparatus according to claim 26, wherein said sealing member comprises at least one of epoxy resin, silicone resin, urea resin, and glass.
31. (Previously Presented) A light-emitting apparatus according to claim 26, wherein said sealing member is shaped like a bullet.
32. (Previously Presented) A light-emitting apparatus according to claim 26, wherein a concentration of at least one of said first fluorescent material and said second fluorescent material changes within said fluorescent material resin, as a function of distance to said GaN semiconductor light-emitting device.
33. (Previously Presented) A light-emitting apparatus according to claim 26, wherein said fluorescent material resin and said sealing member comprise one material.
34. (Previously Presented) A light-emitting apparatus according to claim 26, wherein said GaN semiconductor light-emitting device comprises a chip.
35. (Canceled)
36. (Canceled)

37. (Canceled)

38. (Previously Presented) The light-emitting apparatus according to claim 1, wherein a substrate of said GaN semiconductor light-emitting device comprises sapphire.

39. (Previously Presented) The light-emitting apparatus according to claim 11, wherein a substrate of said GaN semiconductor light-emitting device comprises sapphire.

40. (Previously Presented) The light-emitting apparatus according to claim 21, wherein a substrate of said GaN semiconductor light-emitting device comprises sapphire.

41. (Previously Presented) A light-emitting apparatus according to claim 21, wherein said third light source includes a second fluorescent material that absorbs said blue light emitted by said first light source and emits said red light.

42. (Previously Presented) A light-emitting apparatus, comprising:

a box including a cup portion including a bottom surface, said bottom surface including a first electrode and a second electrode;

a primary light source including a GaN semiconductor light-emitting device that emits a first light of a wavelength of 380 nm to 500 nm and is fixed to one of said first electrode and said second electrode, said GaN semiconductor light-emitting device, including:

a single reflective layer; and

a transparent electrode disposed above said single reflective layer; and

a secondary light source including a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; Y₂O₂S:Ce; and ZnS:Cu, and a resin, said fluorescent material being dispersed within said resin, and said resin being contained in said cup portion,

wherein said fluorescent material absorbs light of said first wavelength and emits light of a second wavelength, which is greater than said first wavelength.

43. (Previously Presented) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

a red LED, a green LED, and a blue LED; and
a light-emitting apparatus, according to claim 1, that emits white light.

44. (Previously Presented) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

a red LED, a green LED, and a blue LED; and
a light-emitting apparatus, according to claim 11, that emits white light.

45. (Previously Presented) A display device, comprising a plurality of light-emitting device (LED) units, wherein each of said plurality of LED units comprises:

a red LED, a green LED, and a blue LED;
a light-emitting apparatus, according to claim 41, that emits white light.

46. (Previously Presented) A vehicular signal display device comprising a plurality of light-emitting apparatuses according to claim 1, wherein said plurality of light-emitting apparatuses comprise a matrix, a portion of said matrix being controlled by a controller, which turns said portion on or off.

47. (Canceled)

48. (Canceled)

49. (Previously Presented) A light-emitting apparatus according to claim 1, wherein said fluorescent material is dispersed in a fluorescent material layer disposed above said sealing member and absorbs said first light of a first wavelength and emits a second light of a second wavelength, which is greater than said first wavelength.

50. (Previously Presented) A light-emitting apparatus according to claim 41, wherein said fluorescent material resin comprises a first fluorescent material resin and a second fluorescent material resin, said first fluorescent material is dispersed in said first fluorescent material resin, which is disposed directly above said GaN semiconductor light-emitting device, and said second fluorescent material is dispersed in said second fluorescent material resin, which is disposed on said first fluorescent material resin.

51. (Previously Presented) A light-emitting apparatus according to claim 1, wherein said light-emitting layer comprises a multiple quantum well structure.

52. (Previously Presented) A light-emitting apparatus according to claim 51, wherein said multiple quantum well structure comprises well layers comprised of InGaN.

53. (Previously Presented) A light-emitting apparatus according to claim 11, wherein said light-emitting layer comprises a multiple quantum well structure.

54. (Previously Presented) A light-emitting apparatus according to claim 53, wherein said multiple quantum well structure comprises well layers comprised of InGaN.

55. (Previously Presented) A light-emitting apparatus according to claim 21, wherein said light-emitting layer comprises a multiple quantum well structure.

56. (Previously Presented) A light-emitting apparatus according to claim 55, wherein said multiple quantum well structure comprises well layers comprised of InGaN.

57. (Previously Presented) A light-emitting apparatus according to claim 42, wherein said light-emitting layer comprises a multiple quantum well structure.

58. (Previously Presented) A light-emitting apparatus according to claim 57, wherein said multiple quantum well structure comprises well layers comprised of InGaN.

59. (Previously Presented) A light-emitting apparatus according to claim 1, wherein said single reflective layer is directly disposed on said surface of said substrate and said surface is opposite to a side wherein said light-emitting layer is located.

60. (Previously Presented) A light-emitting apparatus according to claim 11, wherein said single reflective layer is directly disposed on said surface of said substrate and said surface is opposite to a side wherein said light-emitting layer is located.

61. (Previously Presented) A light-emitting apparatus according to claim 21, wherein said single reflective layer is directly disposed on said surface of said substrate and said surface is opposite to a side wherein said light-emitting layer is located.

62. (Previously Presented) A light-emitting apparatus according to claim 42, wherein said single reflective layer is directly disposed on said surface of said substrate and said surface is opposite to a side wherein said light-emitting layer is located.

63. (New) A light-emitting apparatus, comprising:

a primary light source comprising a GaN semiconductor light-emitting device that emits a first light of a wavelength of 380 nm to 500 nm, said GaN semiconductor light-emitting device comprising:

a single reflective layer; and

a transparent electrode disposed above said single reflective layer; and

a leadframe comprising a cup portion including a bottom surface on which said GaN semiconductor light-emitting device is mounted;

a secondary light source comprising a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; ZnS:Cu; and Y₂O₂S:Ce, and a fluorescent material resin, said fluorescent material being dispersed within said fluorescent material resin, and said fluorescent material resin being contained in said cup portion; and

a sealing member that focuses light emitted from said light-emitting apparatus, said sealing member being disposed above said secondary light source,

wherein said fluorescent material absorbs said first light of a first wavelength and emits a second light of a second wavelength, which is greater than said first wavelength, wherein said light-emitting layer comprises a multiple quantum well structure, wherein said multiple quantum well structure comprises well layers comprised of InGa_N, and

wherein said single reflective layer is directly disposed on said surface of said substrate and said surface is opposite to a side wherein said light-emitting layer is located.

64. (New) A light-emitting apparatus, comprising:

a primary light source comprising a GaN semiconductor light-emitting device that emits a first light of a wavelength of 380 nm to 500 nm, said GaN semiconductor light-emitting device, comprising:

a single reflective layer; and

a transparent electrode disposed above said single reflective layer; and

a leadframe comprising a cup portion including a bottom surface on which said GaN semiconductor light-emitting device is mounted;

a secondary light source comprising a fluorescent material that comprises at least one of ZnS:Eu and Y₂O₂S:Ce, and a fluorescent material resin, said fluorescent material being dispersed within said fluorescent material resin, and said fluorescent material resin being contained in said cup portion; and

a sealing member that focuses light emitted from said light-emitting apparatus, said sealing member being disposed above said secondary light source,

wherein said fluorescent material absorbs said first light of a first wavelength and emits said second light of a second wavelength, which is greater than said first wavelength, wherein said light-emitting layer comprises a multiple quantum well structure, and wherein said multiple quantum well structure comprises well layers comprised of InGa_N.

65. (New) A light-emitting apparatus, comprising:

a first light source comprising a GaN semiconductor light-emitting device that emits a blue light, said GaN semiconductor light-emitting device, comprising:

a single reflective layer; and

a transparent electrode disposed above said single reflective layer; and

a leadframe comprising a cup portion including a bottom surface on which said GaN semiconductor light-emitting device is mounted;

a second light source including a first fluorescent material that absorbs said blue light emitted by said first light source and emits a green light and a fluorescent material resin, said first fluorescent material being dispersed within said fluorescent material resin, and said fluorescent material resin being contained in said cup portion;

a sealing member that focuses light emitted from said light-emitting apparatus, said sealing member being disposed above said secondary light source; and

a third light source that emits a red light,

wherein said blue light emitted by said first light source, said green light emitted by said second light source, and said red light emitted by said third light source are mixed to thereby generate white light,

wherein said light-emitting layer comprises a multiple quantum well structure, and

wherein said multiple quantum well structure comprises well layers comprised of InGaN.

66. (New) A light-emitting apparatus, comprising:

a box including a cup portion including a bottom surface, said bottom surface including a first electrode and a second electrode;

a primary light source including a GaN semiconductor light-emitting device that emits a first light of a wavelength of 380 nm to 500 nm and is fixed to one of said first electrode and said second electrode, said GaN semiconductor light-emitting device, including:

a single reflective layer; and

a transparent electrode disposed above said single reflective layer; and

a secondary light source including a fluorescent material that comprises at least one of ZnS:Cu, Au, Al; ZnS:Cu, Al; $Y_2O_3S:Ce$; and ZnS:Cu, and a resin, said fluorescent material being dispersed within said resin, and said resin being contained in said cup portion,

wherein said fluorescent material absorbs light of said first wavelength and emits light of a second wavelength, which is greater than said first wavelength

wherein said light-emitting layer comprises a multiple quantum well structure, and

wherein said multiple quantum well structure comprises well layers comprised on InGaN.